



Package: SOT-89

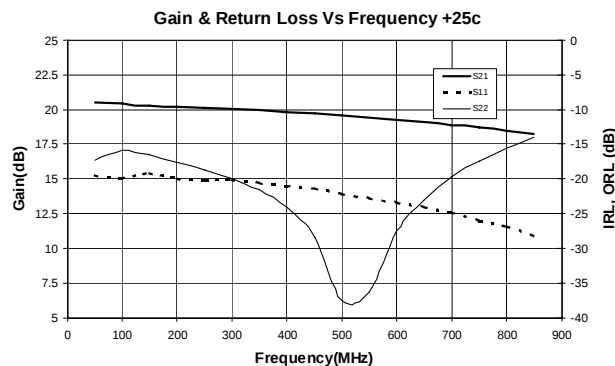


### Product Description

RFMD's SBF-5089(Z) is a high performance InGaP/GaAs Heterojunction Bipolar Transistor MMIC Amplifier. A Darlington configuration designed with InGaP process technology provides broadband performance up to 0.5GHz with excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only a single positive supply voltage, DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.

#### Optimum Technology Matching® Applied

- ☐ GaAs HBT
- ☐ GaAs MESFET
- ☒ InGaP HBT
- ☐ SiGe BiCMOS
- ☐ Si BiCMOS
- ☐ SiGe HBT
- ☐ GaAs pHEMT
- ☐ Si CMOS
- ☐ Si BJT
- ☐ GaN HEMT
- ☐ InP HBT
- ☐ RF MEMS
- ☐ LDMOS



### Features

- Available in RoHS Compliant and Pb-Free (Z Part Number)
- $IP_3 = 41$  dBm at 240MHz
- Stable Gain Over Temperature
- Robust 1000V ESD, Class 1C
- Operates From Single Supply
- Low Thermal Resistance

### Applications

- Receiver IF Applications
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite Terminals

| Parameter                          | Specification |      |      | Unit | Condition        |
|------------------------------------|---------------|------|------|------|------------------|
|                                    | Min.          | Typ. | Max. |      |                  |
| Small Signal Gain                  |               | 20.5 |      | dB   | 70MHz            |
|                                    | 18.5          | 20.0 | 21.5 | dB   | 240MHz           |
|                                    | 18.0          | 19.5 | 21.0 | dB   | 500MHz           |
| Output Power at 1dB Compression    |               | 21   |      | dBm  | 70MHz            |
|                                    |               | 21   |      | dBm  | 240MHz           |
|                                    | 19.2          | 20.7 |      | dBm  | 400MHz           |
| Output Third Order Intercept Point |               | 39.0 |      | dBm  | 70MHz            |
|                                    |               | 41.0 |      | dBm  | 240MHz           |
|                                    | 37.5          | 39.5 |      | dBm  | 400MHz           |
| Input Return Loss                  | 14            | 18   |      | dB   | 500MHz           |
| Output Return Loss                 | 12.0          | 16.0 |      | dB   | 500MHz           |
| Noise Figure                       |               | 2.8  | 3.8  | dB   | 500MHz           |
| Device Operating Voltage           | 4.5           | 4.9  | 5.3  | V    |                  |
| Device Operating Current           | 82            | 90   | 98   | mA   |                  |
| Thermal Resistance                 |               | 43   |      | °C/W | junction to lead |

Test Conditions:  $V_S = 8V$ ,  $I_D = 90mA$  Typ.,  $T_L = 25^\circ C$ .  $OIP_3$  Tone Spacing = 1MHz,  $P_{OUT}$  per tone = 0dBm,  $R_{BIAS} = 33\Omega$ . Data with Application Circuit.

## Absolute Maximum Ratings

| Parameter                           | Rating     | Unit |
|-------------------------------------|------------|------|
| Device Current ( $I_D$ )            | 150        | mA   |
| Device Voltage ( $V_D$ )            | 6          | V    |
| RF Input Power                      | +19        | dBm  |
| Max Operating Dissipated Power      | 0.8        | W    |
| Junction Temp ( $T_J$ )             | +150       | °C   |
| Operating Temp Range ( $T_L$ )      | -40 to +85 | °C   |
| Storage Temp                        | +150       | °C   |
| ESD Rating - Human Body Model (HBM) | Class 1C   |      |
| Moisture Sensitivity Level          | MSL 2      |      |

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

$$I_D V_D < (T_J - T_L) / R_{TH}, j-l \text{ and } T_L = T_{LEAD}$$



**Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

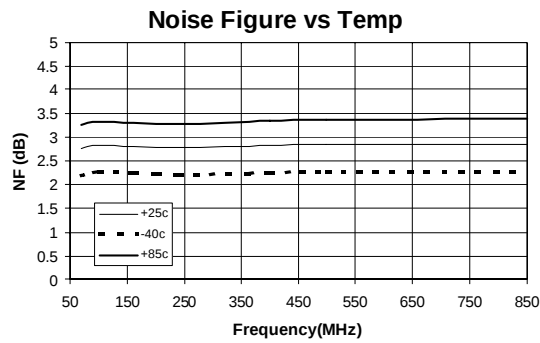
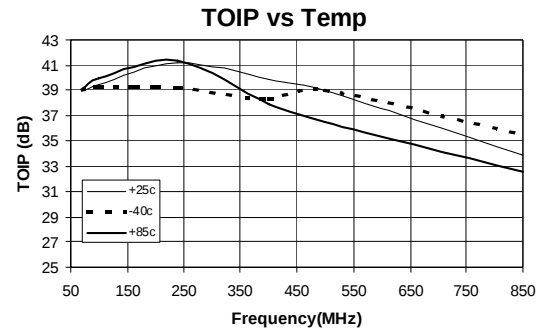
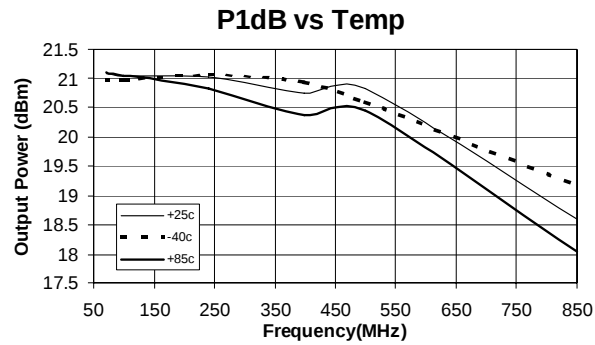
RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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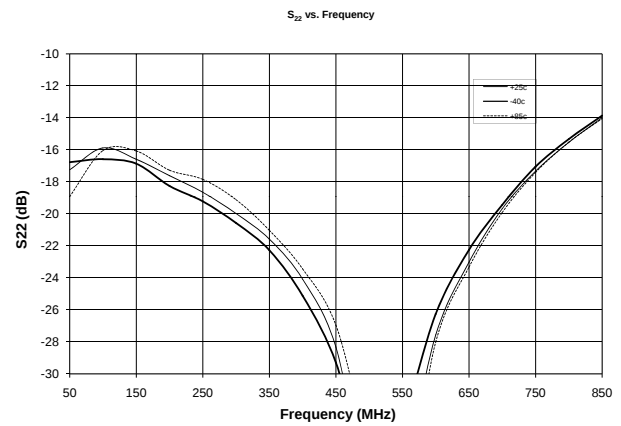
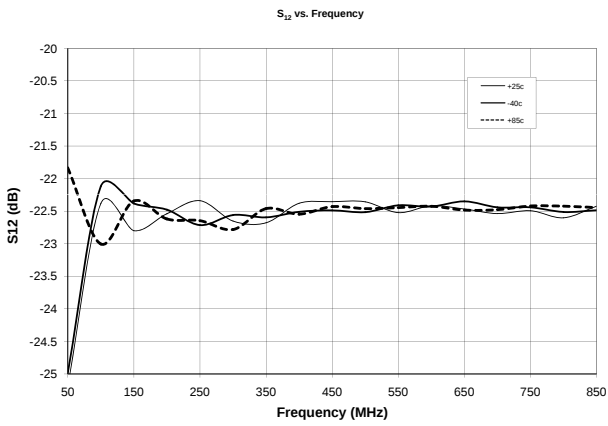
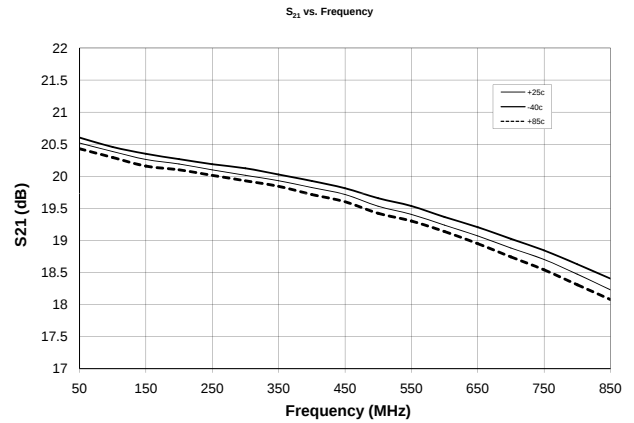
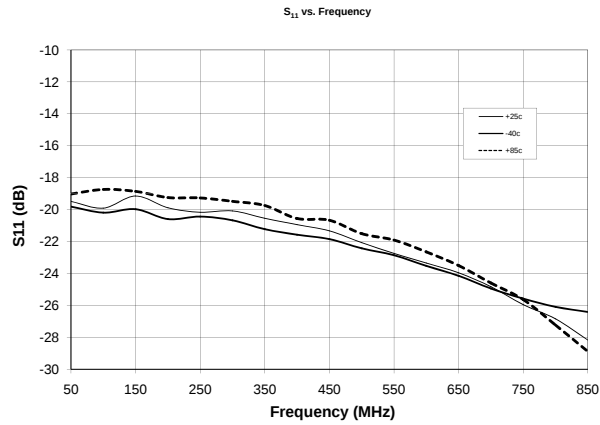
## Typical RF Performance at Key Operating Frequencies

| Parameter                          | Unit | 70MHz | 100MHz | 240MHz | 400MHz | 500MHz | 850MHz |
|------------------------------------|------|-------|--------|--------|--------|--------|--------|
| Small Signal Gain                  | dB   | 20.5  | 20.4   | 20.1   | 19.8   | 19.5   | 18.2   |
| Output Third Order Intercept Point | dBm  | 39    | 39     | 41     | 39.5   | 39     | 34     |
| Output Power at 1dB Compression    | dBm  | 21.0  | 21.0   | 21.0   | 20.7   | 20.8   | 18.6   |
| Input Return Loss                  | dB   | 19.4  | 19.9   | 20.1   | 20.9   | 22.0   | 26.8   |
| Output Return Loss                 | dB   | 17.2  | 15.8   | 18.6   | 24.0   | 37.5   | 15.5   |
| Reverse Isolation                  | dB   | 25.2  | 22.4   | 22.3   | 22.3   | 22.3   | 22.4   |
| Noise Figure                       | dB   | 2.7   | 2.8    | 2.7    | 2.8    | 2.8    | 2.8    |

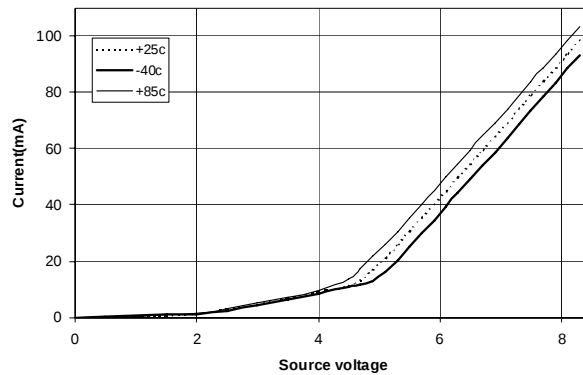
Test Conditions:  $V_S = 8V$ ,  $I_D = 90mA$  Typ., OIP<sub>3</sub> Tone Spacing = 1MHz, P<sub>OUT</sub> per tone = 0dBm.  $T_L = 25^\circ C$ ,  $R_{BIAS} = 33\Omega$ ,  $Z_S = Z_L = 50\Omega$ , App circuit.



Test Conditions:  $V_S = 8V$ ,  $R_{BIAS} = 33\Omega$ ,  $I_D = 90mA$ ,  $T = +25^\circ C$ ,

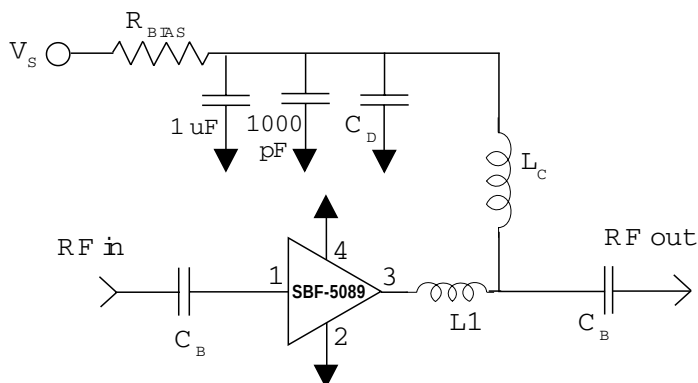


## Bias Sweep vs. Temperature



Note: Output Return Loss can be improved at low end of band with L1 selection.

## Application Circuit Schematic



### Application Circuit Element Values

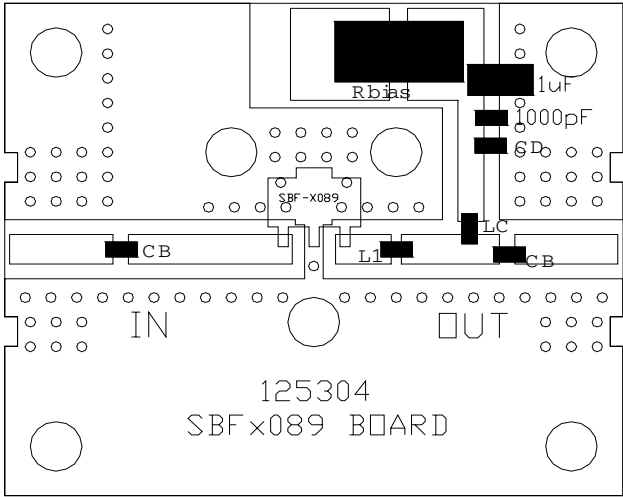
| Reference Designator | 70MHz | 100MHz | 240MHz | 500MHz | 850MHz |
|----------------------|-------|--------|--------|--------|--------|
| C <sub>B</sub>       | 1uF   | 1000pF | 1000pF | 220pF  | 100pF  |
| C <sub>D</sub>       | 1uF   | 100pF  | 100pF  | 100pF  | 68pF   |
| L <sub>C</sub>       | 6.8uH | 1.2uH  | 1.2uH  | 68nH   | 33nH   |
| L1                   | 6.8nH | 6.8nH  | 6.8nH  | 6.8nH  | 6.8nH  |

### Recommended Bias Resistance for I<sub>D</sub>=90mA

|                                          |     |    |    |    |
|------------------------------------------|-----|----|----|----|
| Supply Voltage (V <sub>S</sub> ) (Volts) | 7.5 | 8  | 10 | 12 |
| Bias Resistance (Ω)                      | 27  | 33 | 55 | 77 |

Note=R<sub>BIAS</sub> provides DC bias stability over temperature.

Evaluation Board Layout

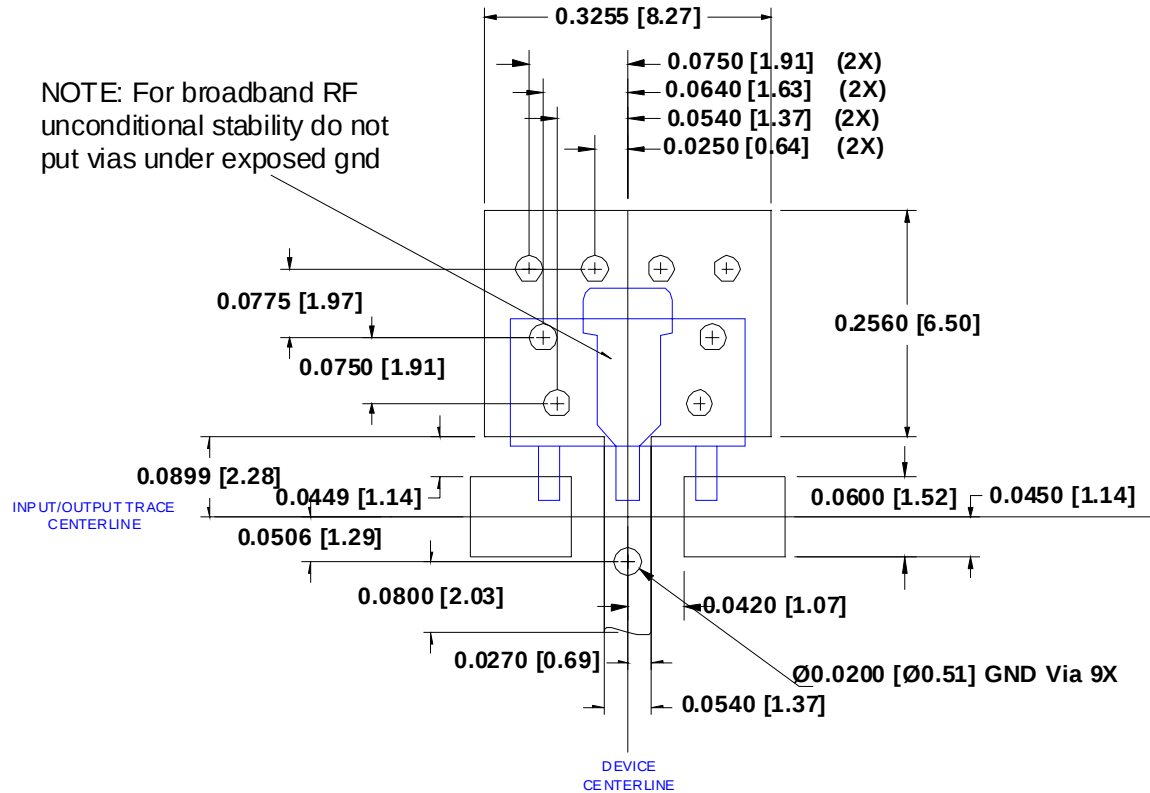


Mounting Instructions

- 1. Note: For broadband RF unconditional stability do not put GND vias under the exposed backside GND paddle.
- 2. Solder the copper pad on the backside of the device package to the ground plane.
- 3. Use a large ground pad area with many plated through-holes as shown.
- 4. We recommend 1 or 2 ounce copper. Measurement for this data sheet were made on a 31mil thick FR-4 board with 1 ounce copper on both sides.

| Pin  | Function    | Description                                                                                                                    |
|------|-------------|--------------------------------------------------------------------------------------------------------------------------------|
| 1    | RF IN       | RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequency of operation.            |
| 2, 4 | GND         | Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.       |
| 3    | RF OUT/BIAS | RF output and bias pin. DC voltage is present on this pin therefore a DC-blocking capacitor is necessary for proper operation. |

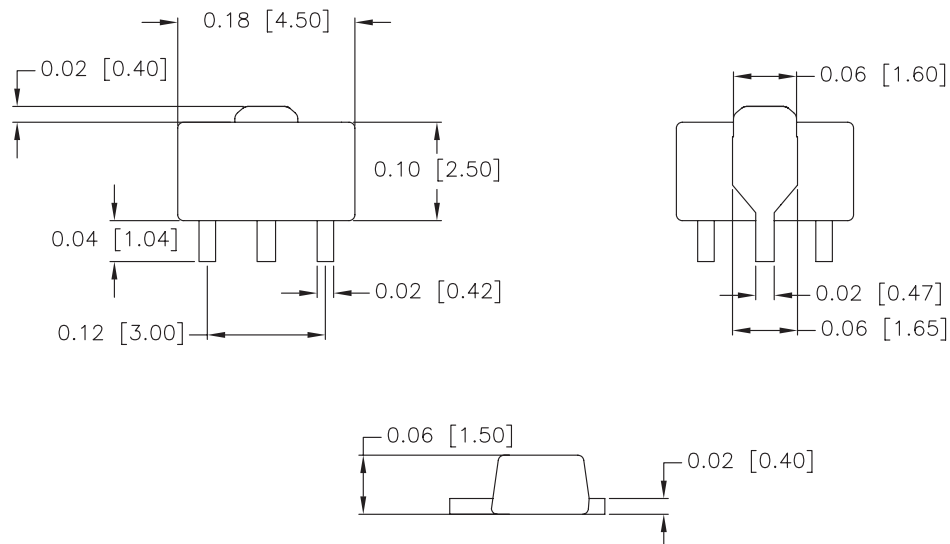
## Suggested Pad Layout



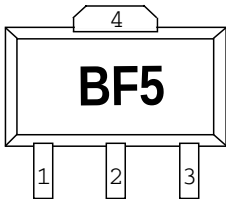
## Package Drawing

Dimensions in inches (millimeters)

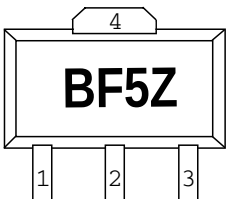
Refer to drawing posted at [www.rfmd.com](http://www.rfmd.com) for tolerances.



Part Identification



Tin-Lead



Lead Free

Alternate marking “SBF5089” or “SBF5089Z” on line one with Trace Code on line two.

Ordering Information

| Part Number | Reel Size | Devices/Reel |
|-------------|-----------|--------------|
| SBF-5089    | 7"        | 1000         |
| SBF-5089Z   | 7"        | 1000         |